



STW80NF55-06

N-CHANNEL 55V - 0.005Ω - 80A TO-247

STripFET™ II POWER MOSFET

PRELIMINARY DATA

TYPE	V _{DSS}	R _{DS(on)}	I _D
STW80NF55-06	55 V	< 0.0065 Ω	80 A

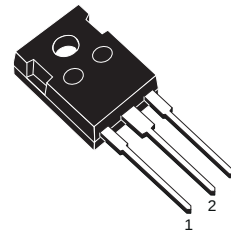
- TYPICAL R_{DS(on)} = 0.005Ω
- EXCEPTIONAL dv/dt CAPABILITY
- 100% AVALANCHE TESTED

DESCRIPTION

This Power MOSFET is the latest development of STMicroelectronics unique "Single Feature Size™" strip-based process. The resulting transistor shows extremely high packing density for low on-resistance, rugged avalanche characteristics and less critical alignment steps therefore a remarkable manufacturing reproducibility.

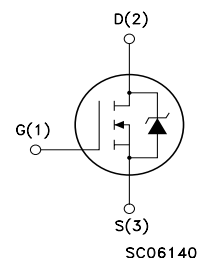
APPLICATIONS

- DC-AC & DC-DC CONVERTERS
- AUTOMOTIVE ENVIRONMENT
- SOLENOID AND RELAY DRIVERS
- MOTOR CONTROL, AUDIO AMPLIFIERS



TO-247

INTERNAL SCHEMATIC DIAGRAM



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V _{DS}	Drain-source Voltage (V _{GS} = 0)	55	V
V _{DGR}	Drain-gate Voltage (R _{GS} = 20 kΩ)	55	V
V _{GS}	Gate- source Voltage	±20	V
I _D (*)	Drain Current (continuous) at T _C = 25°C	80	A
I _D	Drain Current (continuous) at T _C = 100°C	80	A
I _{DM} (●)	Drain Current (pulsed)	320	A
P _{TOT}	Total Dissipation at T _C = 25°C	300	W
	Derating Factor	2	W/°C
E _{AS} (1)	Single Pulse Avalanche Energy	1	J
T _{stg}	Storage Temperature	- 55 to 175	°C
T _j	Max. Operating Junction Temperature		

(●) Pulse width limited by safe operating area

(1) Starting T_j = 25°C, I_D = 40A, V_{DD} = 40V

(*) Current Limited by wire bonding

THERMAL DATA

Rthj-case	Thermal Resistance Junction-case Max	0.5	°C/W
Rthj-amb	Thermal Resistance Junction-ambient Max	62.5	°C/W
T _I	Maximum Lead Temperature For Soldering Purpose	300	°C

ELECTRICAL CHARACTERISTICS (TCASE = 25 °C UNLESS OTHERWISE SPECIFIED)

OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V _{(BR)DSS}	Drain-source Breakdown Voltage	I _D = 250 µA, V _{GS} = 0	55			V
I _{DSS}	Zero Gate Voltage Drain Current (V _{GS} = 0)	V _{DS} = Max Rating V _{DS} = Max Rating, T _C = 125 °C			1 10	µA µA
I _{GSS}	Gate-body Leakage Current (V _{DS} = 0)	V _{GS} = ±20V			±100	nA

ON (1)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V _{GS(th)}	Gate Threshold Voltage	V _{DS} = V _{GS} , I _D = 250µA	2	3	4	V
R _{DS(on)}	Static Drain-source On Resistance	V _{GS} = 10V, I _D = 40 A		0.005	0.0065	Ω

DYNAMIC

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
g _{fs} (1)	Forward Transconductance	V _{DS} > 15 V, I _D = 40 A		50		S
C _{iss}	Input Capacitance	V _{DS} = 25V, f = 1 MHz, V _{GS} = 0		7300		pF
C _{oss}	Output Capacitance			980		pF
C _{rss}	Reverse Transfer Capacitance			250		pF

ELECTRICAL CHARACTERISTICS (CONTINUED)**SWITCHING ON**

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on Delay Time	$V_{DD} = 27.5\text{ V}$, $I_D = 40\text{ A}$		40		ns
t_r	Rise Time	$R_G = 4.7\Omega$, $V_{GS} = 10\text{ V}$ (see test circuit, Figure 3)		240		ns
Q_g	Total Gate Charge	$V_{DD} = 44\text{ V}$, $I_D = 80\text{ A}$,		190	230	nC
Q_{gs}	Gate-Source Charge	$V_{GS} = 10\text{ V}$		40		nC
Q_{gd}	Gate-Drain Charge			65		nC

SWITCHING OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(off)}$	Turn-off-Delay Time	$V_{DD} = 27.5\text{ V}$, $I_D = 40\text{ A}$,		260		ns
t_f	Fall Time	$R_G = 4.7\Omega$, $V_{GS} = 10\text{ V}$ (see test circuit, Figure 3)		75		ns
$t_{d(off)}$	Off-voltage Rise Time	$V_{clamp} = 44\text{ V}$, $I_D = 80\text{ A}$		70		ns
$t_{r(Voff)}$	Off-voltage Rise Time	$R_G = 4.7\Omega$, $V_{GS} = 10\text{ V}$		185		ns
t_f	Fall Time	(see test circuit, Figure 5)		240		ns
t_c	Cross-over Time			110		ns

SOURCE DRAIN DIODE

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I_{SD}	Source-drain Current				80	A
$I_{SDM(2)}$	Source-drain Current (pulsed)				320	A
$V_{SD(1)}$	Forward On Voltage	$I_{SD} = 80\text{ A}$, $V_{GS} = 0$			1.5	V
t_{rr}	Reverse Recovery Time	$I_{SD} = 80\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$,		90		ns
Q_{rr}	Reverse Recovery Charge	$V_{DD} = 20\text{ V}$, $T_j = 150^\circ\text{C}$		0.295		μC
I_{RRM}	Reverse Recovery Current	(see test circuit, Figure 5)		6.5		A

Note: 1. Pulsed: Pulse duration = 300 μs , duty cycle 1.5 %.
 2. Pulse width limited by safe operating area.

Fig. 1: Unclamped Inductive Load Test Circuit

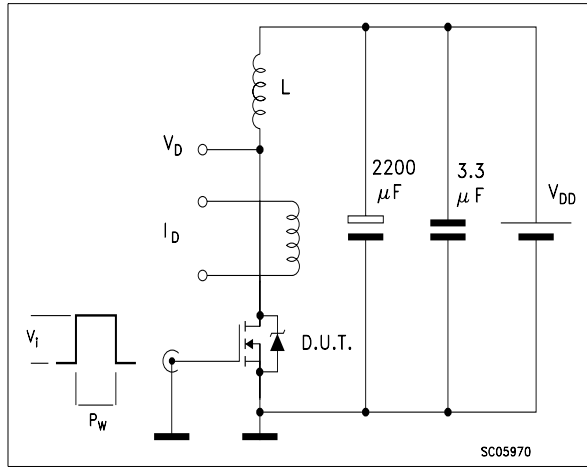


Fig. 2: Unclamped Inductive Waveform

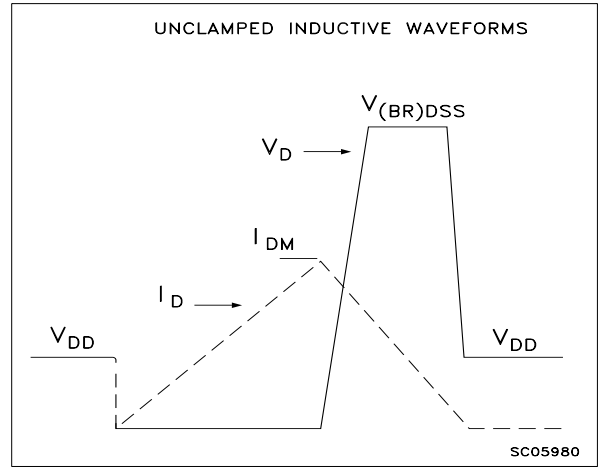


Fig. 3: Switching Times Test Circuit For Resistive Load

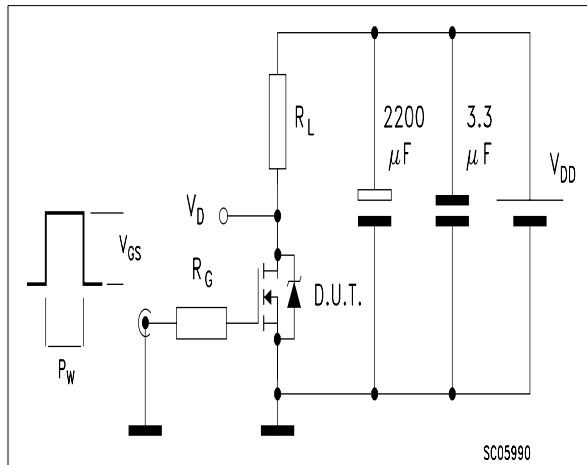


Fig. 4: Gate Charge test Circuit

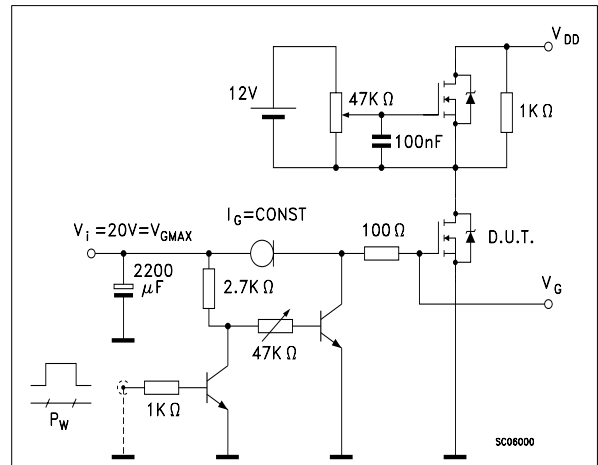
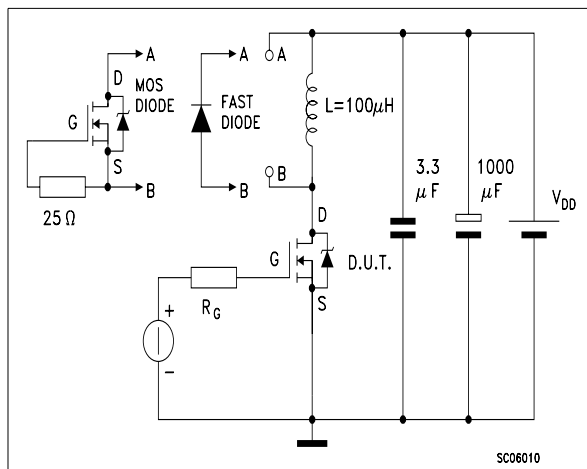
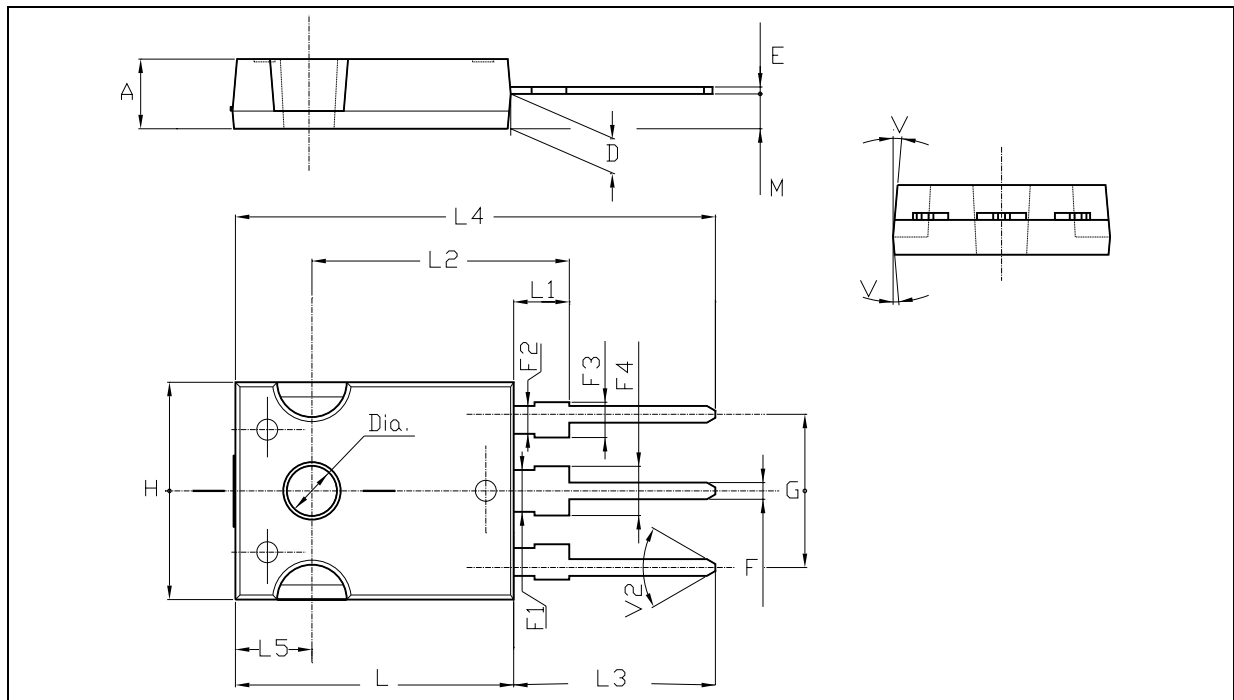


Fig. 5: Test Circuit For Inductive Load Switching And Diode Recovery Times



TO-247 MECHANICAL DATA

DIM.	mm.			inch		
	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
A	4.85		5.15	0.19		0.20
D	2.20		2.60	0.08		0.10
E	0.40		0.80	0.015		0.03
F	1		1.40	0.04		0.05
F1		3			0.11	
F2		2			0.07	
F3	2		2.40	0.07		0.09
F4	3		3.40	0.11		0.13
G		10.90			0.43	
H	15.45		15.75	0.60		0.62
L	19.85		20.15	0.78		0.79
L1	3.70		4.30	0.14		0.17
L2		18.50			0.72	
L3	14.20		14.80	0.56		0.58
L4		34.60			1.36	
L5		5.50			0.21	
M	2		3	0.07		0.11
V		5°			5°	
V2		60°			60°	
Dia	3.55		3.65	0.14		0.143



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